

## N-Channel 100 V (D-S) MOSFET

### DESCRIPTION

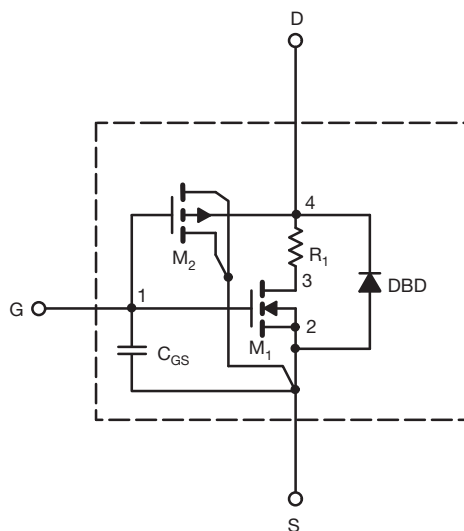
The attached SPICE model describes the typical electrical characteristics of the n-channel vertical DMOS. The subcircuit model is extracted and optimized over the - 55 °C to + 125 °C temperature ranges under the pulsed 0 V to 10 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched  $C_{gd}$  model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

### CHARACTERISTICS

- N-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the - 55 °C to + 125 °C Temperature Range
- Model the Gate Charge

### SUBCIRCUIT MODEL SCHEMATIC



### Note

- This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.



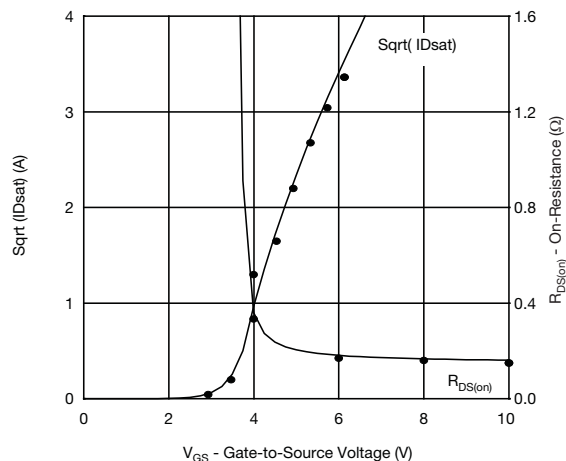
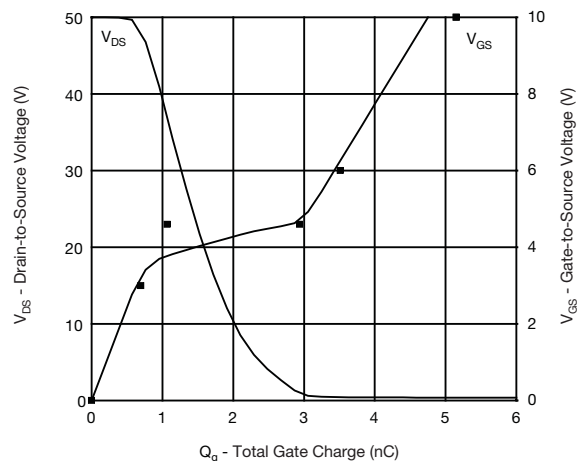
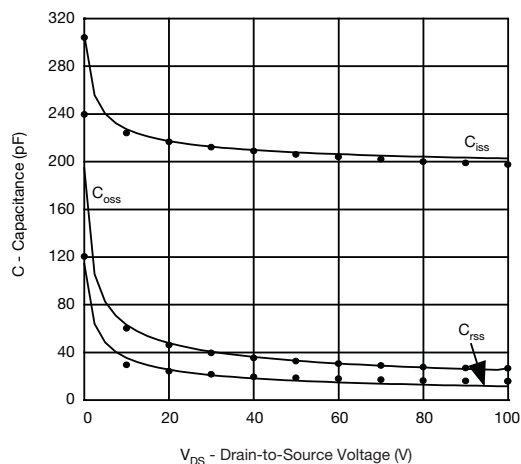
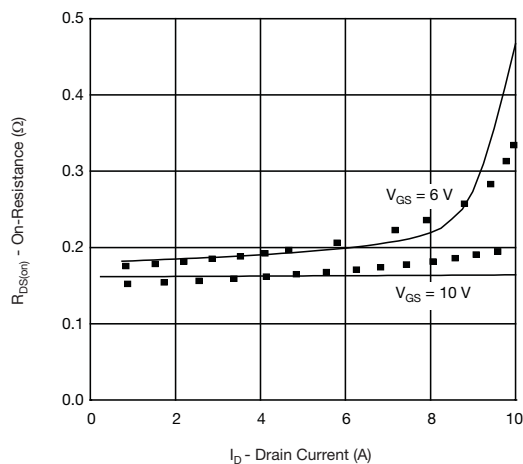
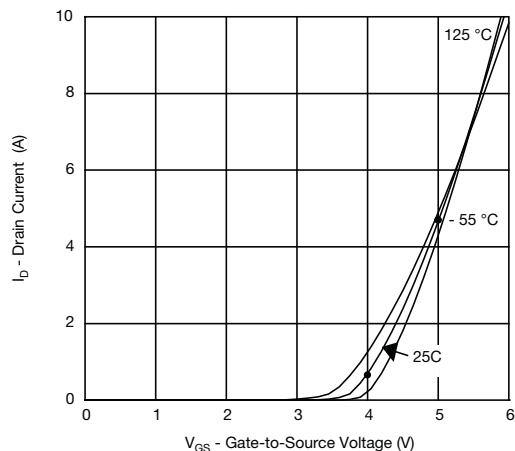
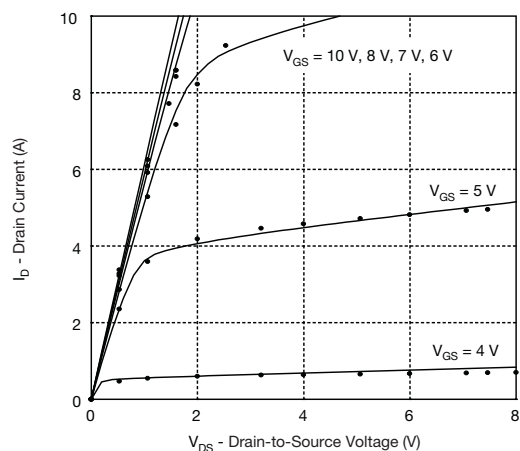
| <b>SPECIFICATIONS</b> ( $T_J = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted) |              |                                                                        |                |               |          |
|--------------------------------------------------------------------------------------|--------------|------------------------------------------------------------------------|----------------|---------------|----------|
| PARAMETER                                                                            | SYMBOL       | TEST CONDITIONS                                                        | SIMULATED DATA | MEASURED DATA | UNIT     |
| <b>Static</b>                                                                        |              |                                                                        |                |               |          |
| Gate-Source Threshold Voltage                                                        | $V_{GS(th)}$ | $V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$                     | 2.6            | -             | V        |
| Drain-Source On-State Resistance <sup>a</sup>                                        | $R_{DS(on)}$ | $V_{GS} = 10\text{ V}$ , $I_D = 2.5\text{ A}$                          | 0.160          | 0.162         | $\Omega$ |
|                                                                                      |              | $V_{GS} = 6\text{ V}$ , $I_D = 2.3\text{ A}$                           | 0.180          | 0.190         |          |
| Forward Transconductance <sup>a</sup>                                                | $g_{fs}$     | $V_{DS} = 10\text{ V}$ , $I_D = 2.5\text{ A}$                          | 4.8            | 5.3           | S        |
| Diode Forward Voltage <sup>a</sup>                                                   | $V_{SD}$     | $I_S = 2.2\text{ A}$                                                   | 0.73           | 0.80          | V        |
| <b>Dynamic<sup>b</sup></b>                                                           |              |                                                                        |                |               |          |
| Total Gate Charge                                                                    | $Q_g$        | $V_{DS} = 50\text{ V}$ , $V_{GS} = 10\text{ V}$ , $I_D = 2.5\text{ A}$ | 4.8            | 5.2           | nC       |
| Gate-Source Charge                                                                   | $Q_{gs}$     |                                                                        | 1.1            | 1.1           |          |
| Gate-Drain Charge                                                                    | $Q_{gd}$     |                                                                        | 1.9            | 1.9           |          |

**Notes**

- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
b. Guaranteed by design, not subject to production testing.



## COMPARISON OF MODEL WITH MEASURED DATA ( $T_J = 25^\circ\text{C}$ , unless otherwise noted)



### Note

- Dots and squares represent measured data.



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